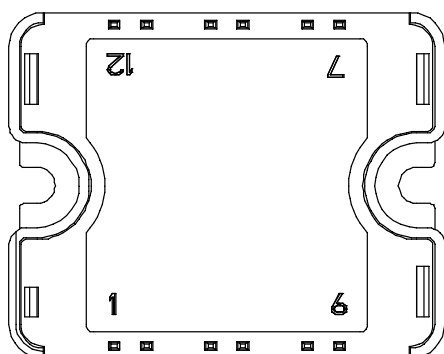
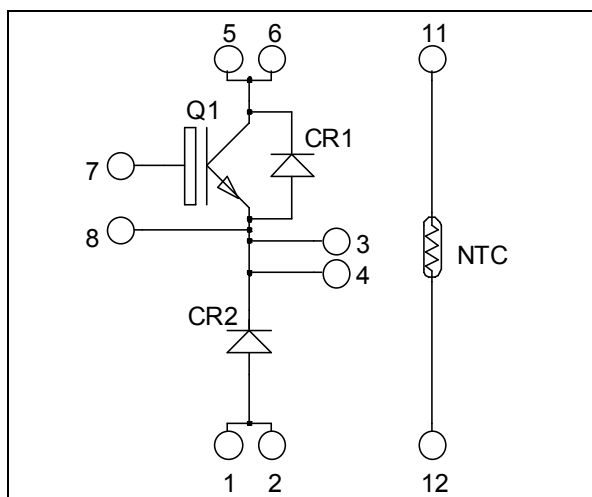


## Buck chopper NPT IGBT Power Module

$$V_{CES} = 1200V$$

$$I_C = 50A @ T_c = 80^{\circ}C$$



Pins 1/2 ; 3/4 ; 5/6 must be shorted together

### Application

- AC and DC motor control
- Switched Mode Power Supplies

### Features

- Non Punch Through (NPT) Fast IGBT
  - Low voltage drop
  - Low tail current
  - Switching frequency up to 50 kHz
  - Soft recovery parallel diodes
  - Low diode VF
  - Low leakage current
  - RBSOA and SCSOA rated
- Very low stray inductance
- Internal thermistor for temperature monitoring
- High level of integration

### Benefits

- Outstanding performance at high frequency operation
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- Solderable terminals both for power and signal for easy PCB mounting
- Low profile
- RoHS Compliant

### Absolute maximum ratings

Symbol	Parameter		Max ratings	Unit
$V_{CES}$	Collector - Emitter Breakdown Voltage		1200	V
$I_C$	Continuous Collector Current	$T_c = 25^{\circ}C$	75	A
		$T_c = 80^{\circ}C$	50	
$I_{CM}$	Pulsed Collector Current	$T_c = 25^{\circ}C$	150	
$V_{GE}$	Gate - Emitter Voltage		$\pm 20$	V
$P_D$	Maximum Power Dissipation	$T_c = 25^{\circ}C$	312	W
RBSOA	Reverse Bias Safe Operating Area	$T_j = 150^{\circ}C$	100A @ 1200V	

**CAUTION:** These Devices are sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed. See application note APT0502 on [www.microsemi.com](http://www.microsemi.com)

**All ratings @  $T_j = 25^\circ\text{C}$  unless otherwise specified**

**Electrical Characteristics**

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
$I_{CES}$	Zero Gate Voltage Collector Current	$V_{GE} = 0\text{V}$ $V_{CE} = 1200\text{V}$	$T_j = 25^\circ\text{C}$ $T_j = 125^\circ\text{C}$		250 500	$\mu\text{A}$
$V_{CE(sat)}$	Collector Emitter saturation Voltage	$V_{GE} = 15\text{V}$ $I_C = 50\text{A}$	$T_j = 25^\circ\text{C}$ $T_j = 125^\circ\text{C}$	3.2 4.0	3.7	V
$V_{GE(th)}$	Gate Threshold Voltage	$V_{GE} = V_{CE2}$ , $I_C = 1\text{mA}$		4.5	6.5	V
$I_{GES}$	Gate – Emitter Leakage Current	$V_{GE} = 20\text{V}$ , $V_{CE} = 0\text{V}$			100	nA

**Dynamic Characteristics**

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
$C_{ies}$	Input Capacitance	$V_{GE} = 0\text{V}$		3450		pF
$C_{oes}$	Output Capacitance	$V_{CE} = 25\text{V}$		330		
$C_{res}$	Reverse Transfer Capacitance	$f = 1\text{MHz}$		220		
$Q_g$	Total gate Charge	$V_{GS} = 15\text{V}$		330		nC
$Q_{ge}$	Gate – Emitter Charge	$V_{Bus} = 600\text{V}$		35		
$Q_{gc}$	Gate – Collector Charge	$I_C = 50\text{A}$		200		
$T_{d(on)}$	Turn-on Delay Time	Inductive Switching ( $25^\circ\text{C}$ )		35		ns
$T_r$	Rise Time	$V_{GE} = 15\text{V}$		65		
$T_{d(off)}$	Turn-off Delay Time	$V_{Bus} = 600\text{V}$		320		
$T_f$	Fall Time	$I_C = 50\text{A}$ $R_G = 5\ \Omega$		30		
$T_{d(on)}$	Turn-on Delay Time	Inductive Switching ( $125^\circ\text{C}$ )		35		ns
$T_r$	Rise Time	$V_{GE} = \pm 15\text{V}$		65		
$T_{d(off)}$	Turn-off Delay Time	$V_{Bus} = 600\text{V}$		360		
$T_f$	Fall Time	$I_C = 50\text{A}$ $R_G = 5\ \Omega$		40		
$E_{on}$	Turn-on Switching Energy	$V_{GE} = \pm 15\text{V}$ $V_{Bus} = 600\text{V}$	$T_j = 125^\circ\text{C}$	6.9		mJ
$E_{off}$	Turn-off Switching Energy	$I_C = 50\text{A}$ $R_G = 5\ \Omega$	$T_j = 125^\circ\text{C}$	3.05		

**Chopper diode ratings and characteristics**

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
$V_{RRM}$	Maximum Peak Repetitive Reverse Voltage		1200			V
$I_{RM}$	Maximum Reverse Leakage Current	$V_R = 1200\text{V}$	$T_j = 25^\circ\text{C}$ $T_j = 125^\circ\text{C}$		100 500	$\mu\text{A}$
$I_F$	DC Forward Current		$T_c = 80^\circ\text{C}$	60		A
$V_F$	Diode Forward Voltage	$I_F = 60\text{A}$		2.5	3	V
		$I_F = 120\text{A}$		3		
		$I_F = 60\text{A}$ , $T_j = 125^\circ\text{C}$		1.8		
$t_{rr}$	Reverse Recovery Time	$I_F = 60\text{A}$	$T_j = 25^\circ\text{C}$ $T_j = 125^\circ\text{C}$	265 350		ns
$Q_{rr}$	Reverse Recovery Charge	$V_R = 800\text{V}$ $di/dt = 200\text{A}/\mu\text{s}$	$T_j = 25^\circ\text{C}$ $T_j = 125^\circ\text{C}$	560 2890		nC

**Thermal and package characteristics**

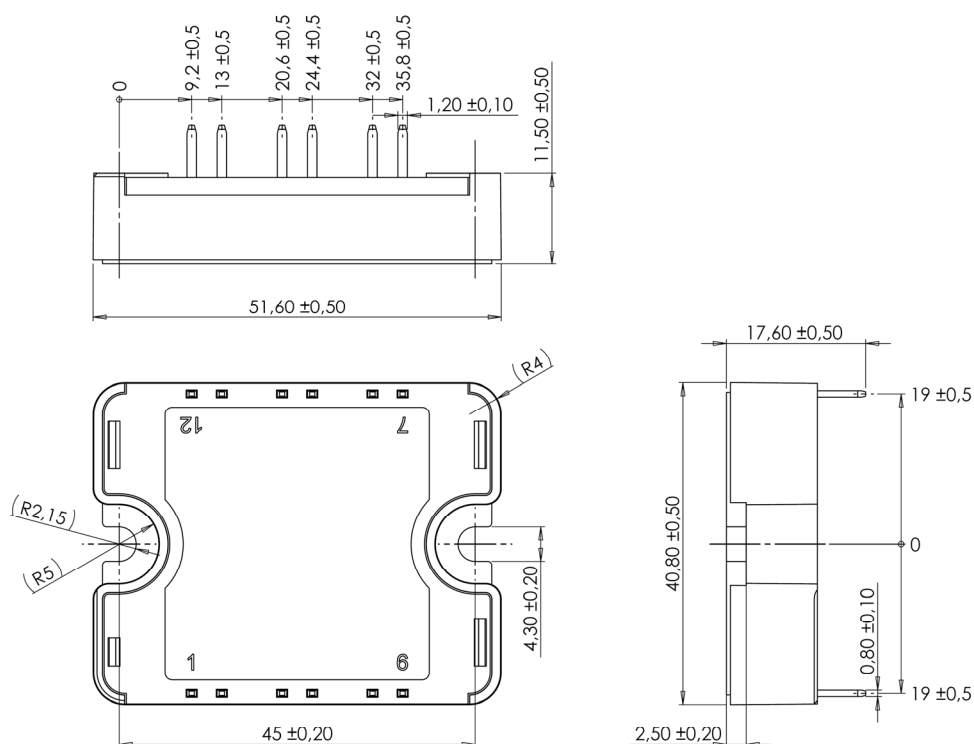
Symbol	Characteristic		Min	Typ	Max	Unit
R <sub>thJC</sub>	Junction to Case Thermal Resistance	IGBT			0.4	°C/W
		Diode			0.9	
V <sub>ISOL</sub>	RMS Isolation Voltage, any terminal to case t=1 min, 50/60Hz		4000			V
T <sub>J</sub>	Operating junction temperature range		-40		150	°C
T <sub>STG</sub>	Storage Temperature Range		-40		125	
T <sub>C</sub>	Operating Case Temperature		-40		100	
Torque	Mounting torque	To heatsink	M4	2	3	N.m
Wt	Package Weight				80	g

**Temperature sensor NTC** (see application note APT0406 on [www.microsemi.com](http://www.microsemi.com) for more information).

Symbol	Characteristic	Min	Typ	Max	Unit
R <sub>25</sub>	Resistance @ 25°C		50		kΩ
B <sub>25/85</sub>	T <sub>25</sub> = 298.15 K		3952		K

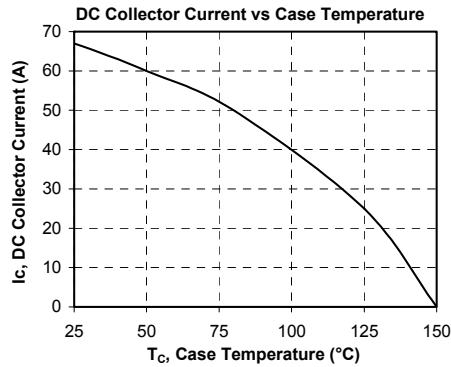
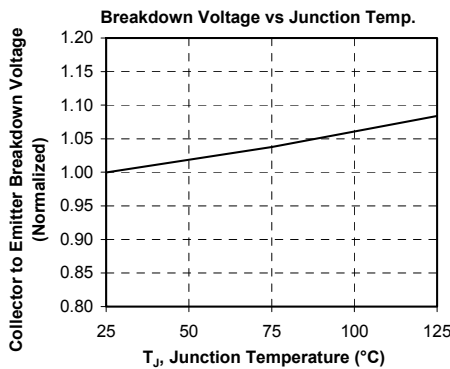
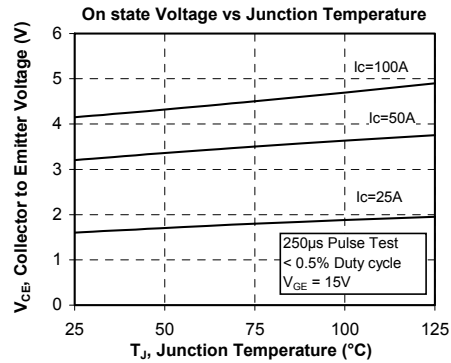
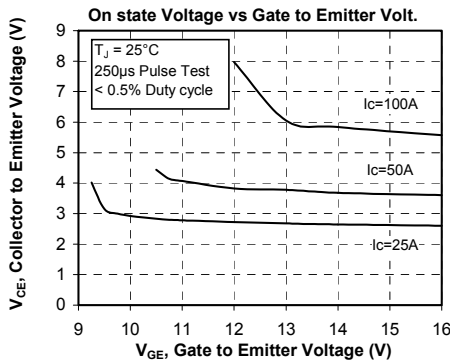
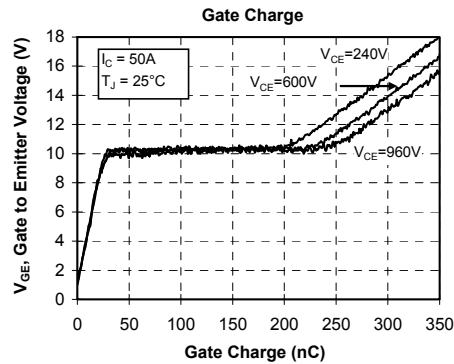
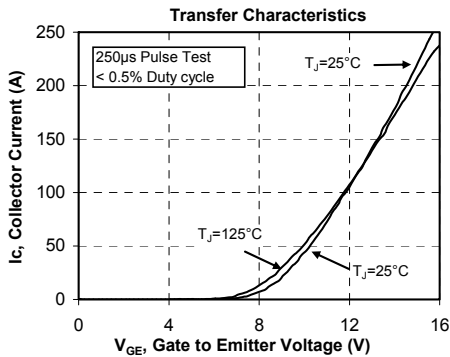
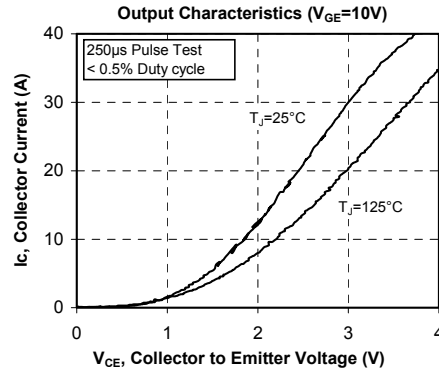
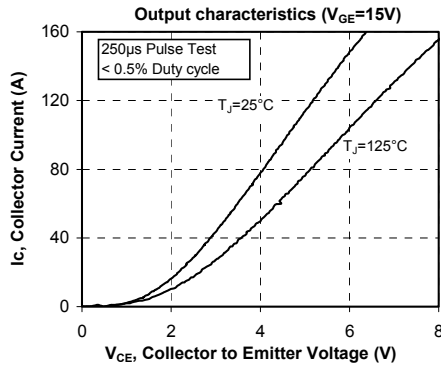
$$R_T = \frac{R_{25}}{\exp \left[ B_{25/85} \left( \frac{1}{T_{25}} - \frac{1}{T} \right) \right]}$$

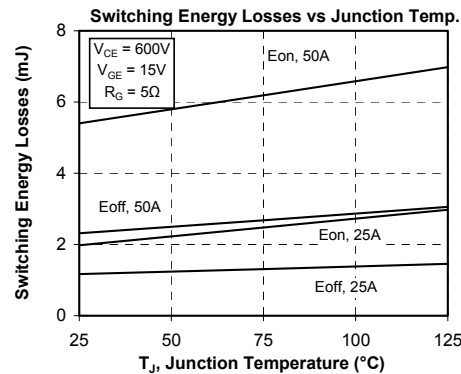
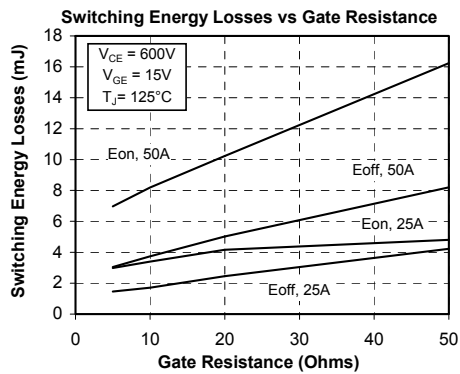
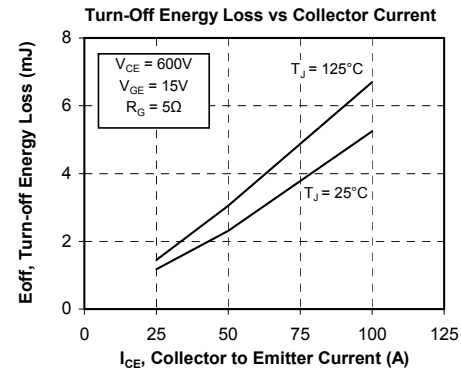
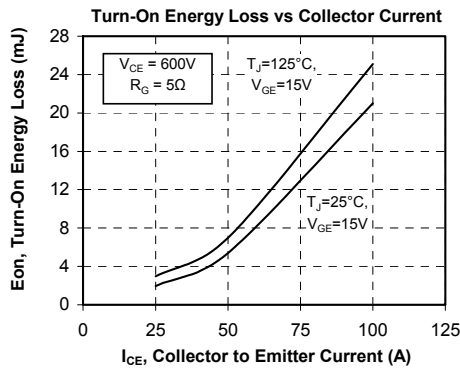
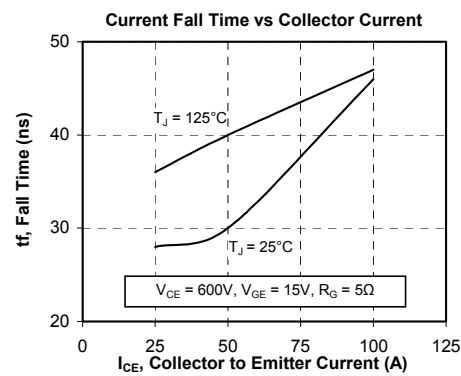
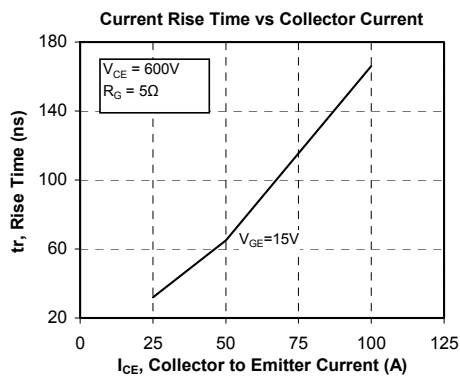
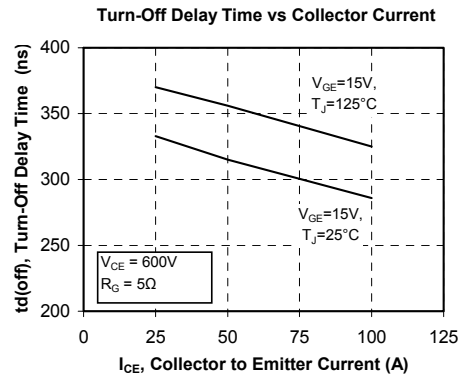
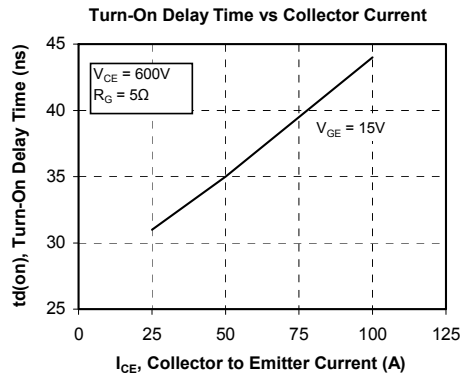
T: Thermistor temperature  
 R<sub>T</sub>: Thermistor value at T

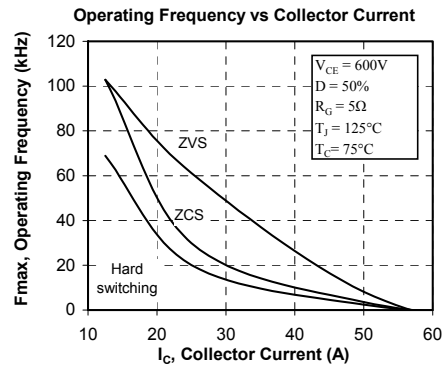
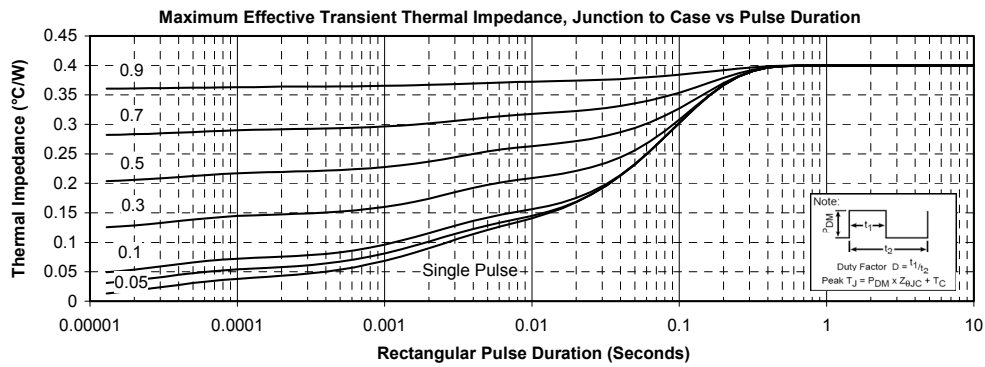
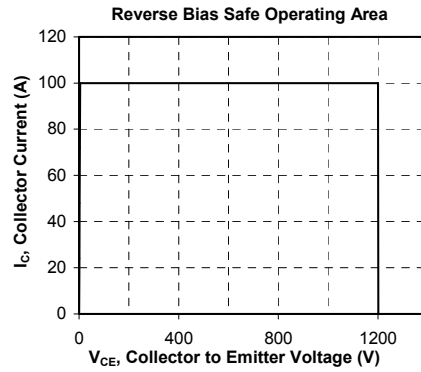
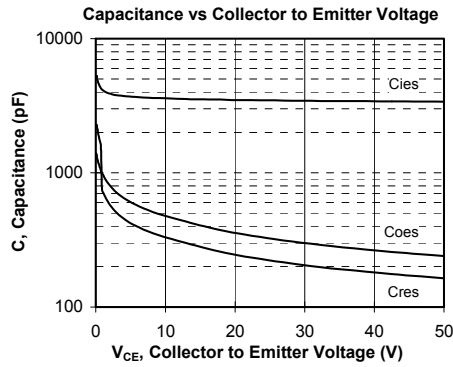
**SP1 Package outline** (dimensions in mm)


See application note 1904 - Mounting Instructions for SP1 Power Modules on [www.microsemi.com](http://www.microsemi.com)

## Typical Performance Curve







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